Switching (30V, 12A)

RSS120N03

Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small and Surface Mount Package (SOP8).

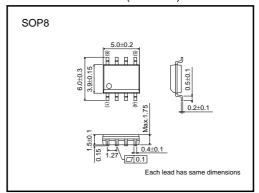
Applications

Power switching, DC / DC converter.

●Structure

Silicon N-channel MOS FET

●External dimensions (Unit : mm)

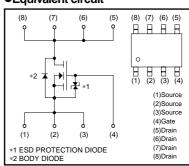


● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V _{DSS}	30	V	
Gate-source voltage		V _{GSS}	20	V	
Drain current	Continuous	lσ	±12	Α	
	Pulsed	I _{DP}	±48	A *1	
Source current (Body diode)	Continuous	Is	1.6	Α	
	Pulsed	I _{SP}	6.4	A *1	
Total power dissipatino		P _D	2	W *2	
Channel temperature		Tch	150	°C	
Strage temperature		Tstg	-55 to +150	°C	
*1 Duc10us Duty ovoloc19/					

^{*1} Pw≤10μs, Duty cycle≤1% *2 MOUNTED ON A CERAMIC BOARD

●Equivalent circuit



*A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use the protection circuit when the fixed voltages are exceeded.

●Thermal resistance (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Channel to ambient	Rth (ch-a)	62.5	°C / W *	

^{*}MOUNTED ON A CERAMIC BOARD

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	10	μΑ	Vgs=20V, Vds=0V
Drain-source breakdown voltage	V _{(BR) DSS}	30	_	_	٧	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	_	_	1	μΑ	V _{DS} =30V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	_	2.5	٧	V _{DS} =10V, I _D =1mA
Static drain-source on-starte resistance	R _{DS} (on)	_	7.1	10.0	mΩ	I _D =12A, V _{GS} =10V
		_	9.4	13.2		I _D =12A, V _{GS} =4.5V
		_	10.2	14.3		I _D =12A, V _{GS} =4V
Forward transfer admittance	Y _{fs} *	9.0	_	_	S	I _D =12A, V _{DS} =10V
Input capacitance	Ciss	_	1360	_	pF	V _{DS} =10V
Output capacitance	Coss	_	430	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	260	_	pF	f=1MHz
Tum-on delay time	t _{d (on)} *	-	10	_	ns	I _D =6A, V _{DD} ≒15V
Rise time	tr *	_	17	_	ns	V _{GS} =10V
Tum-off delay time	t _{d (off)} *	-	63	_	ns	R _L =2.50Ω
Fall time	t _f *	-	26	_	ns	R _{GS} =10Ω
Total gate charge	Qg *	-	18	25	nC	V _{DD} ≒15V
Gate-source charge	Q _{gs} *	_	3.6	_	nC	V _{GS} =5V
Gate-drain charge	Q _{gd} *	_	7.4	_	nC	I _D =12A

^{*}Pulsed

●Body diode characteristics (Source-Drain Characteristics) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp *	-	-	1.2	٧	Is=6.4A, Vgs=0V

^{*}Pulsed

Electrical characteristic curves

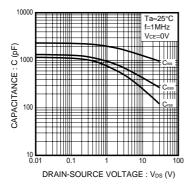


Fig.1 Typical Capacitance vs. Drain-Source Voltage

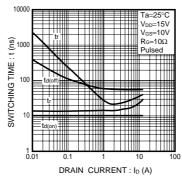


Fig.2 Switching Characteristics

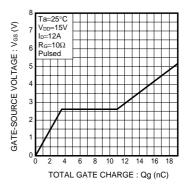


Fig.3 Dynamic Input Characteristics

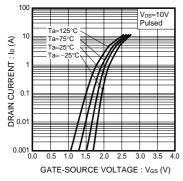


Fig.4 Typical Transfer Characteristics

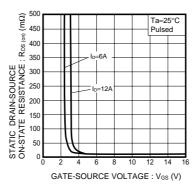


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

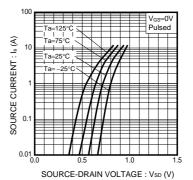


Fig.6 Source Current vs. Source-Drain Voltage

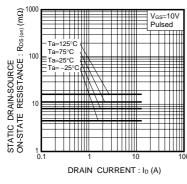


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

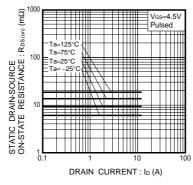


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

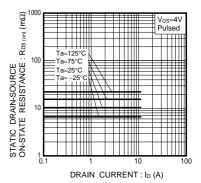


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

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